

/ Descriptions

WR0<50 P ММ Ё QSQ æ Ñ ç s ll 1 Silicon NPN transistor in a TO-92LM Plastic Package.

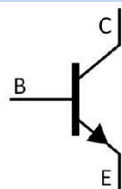
/ Features

т = я ъ H/Ä Н`Н ж ~ /ъ NWD45;4 Й ´
Low saturation voltage, high speed switching time, complementary to KTA1281.

/ Applications

т т I ' ѿ z /ç ð Ä Н
Power amplifier and switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	O	Y
h _{FE} Range	70~140	120~240

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Emitter Current - Continuous	I_E	-2.0	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	

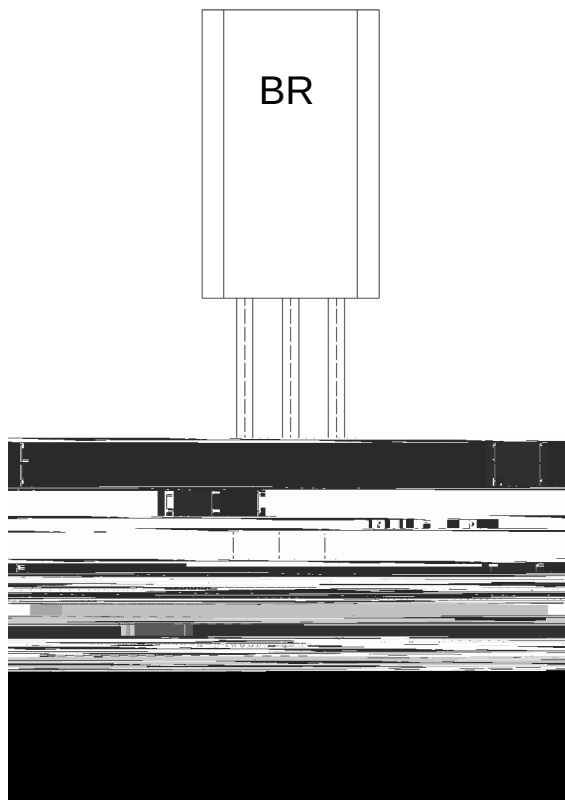
Storage Temperature Range

T_{stg}

Top Secret (TS) / 1 Tf1009.14-1390

/ Electrical Characteristic Curve

/ Marking Instructions



公司代码

EU:

公司代码

F653<:

公司代码

R:

公司代码

公司代码

Note:

BR:

Company Code.

C3209:

Product Type.

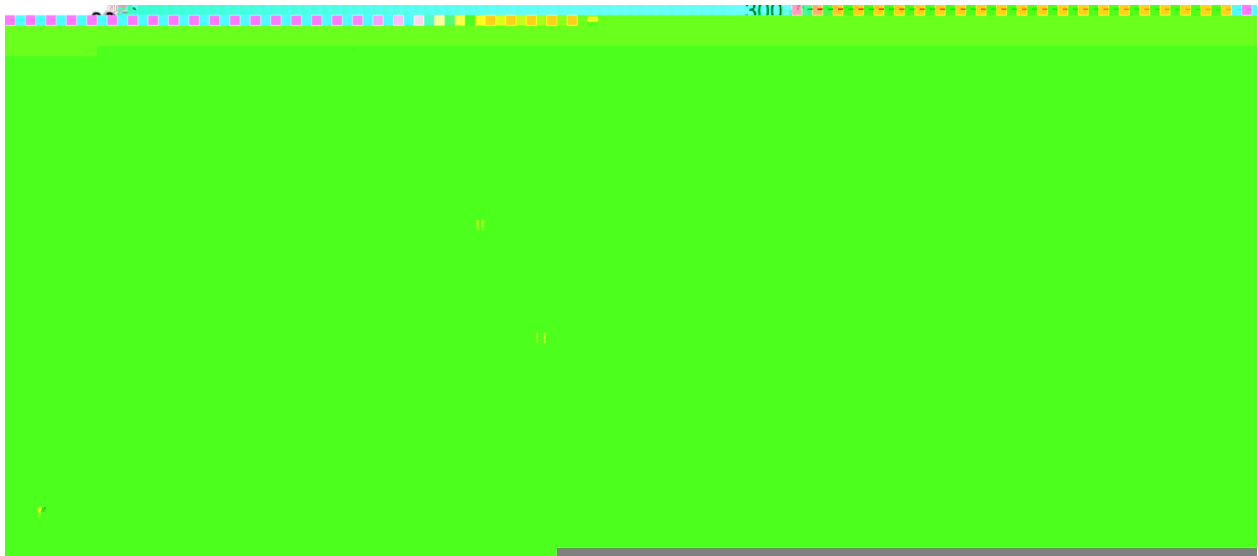
O:

h_{FE} Classifications Symbol

****:

Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



说明

1. 预加热: 25~150 °C, 时间: 60~90sec;
2. 峰值温度: 255 °C, 持续时间: 5 °C 0.5sec;
3. 冷却速度: 2~10 °C /sec.

Note:

- 1.Preheating:25~150 °C , Time:60~90sec.
- 2.Peak Temp.:255 °C , Duration:5 °C 0.5sec.
3. Cooling Speed: 2~10 °C /sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270 °C ± 5 °C 时间: 10 ± 1 sec. Temp.: 270 °C ± 5 °C Time: 10 ± 1 sec

/ Packaging SPEC.

散装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱

纸带 / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只纸带	纸带盒	纸带层盒	盒箱	只箱	盒	箱
							小箱 大箱

/ Notices